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# 2SK3044

# Silicon N-Channel Power F-MOS FET

#### Features

- WWW.DZSC.COM ● Avalanche energy capacity guaranteed: EAS > 130mJ
- $V_{GSS} = \pm 30V$  guaranteed
- High-speed switching:  $t_f = 50$ ns
- No secondary breakdown

#### Applications

- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

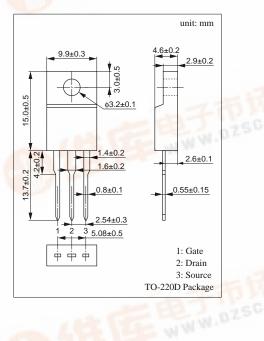
## Absolute Maximum Ratings ( $T_c = 25^{\circ}C$ )

Parameter		Symbol	Ratings	Unit	
Drain to Source breakdown voltage		V <sub>DSS</sub>	450	V	
Gate to Source voltage		V <sub>GSS</sub>	±30	V	
Drain current	DC	I <sub>D</sub> ±7		A	
	Pulse	I <sub>DP</sub>	I <sub>DP</sub> ±14		
Avalanche energy capacity		EAS*	100	mJ	
Allowable power	$T_C = 25^{\circ}C$	D	40	W	
dissipation	$Ta = 25^{\circ}C$	P <sub>D</sub>	2		
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature		T <sub>stg</sub>	-55 to +150	°C	

\*  $L = 4.1 \text{mH}, I_L = 8 \text{A}, V_{DD} = 50 \text{V}, 1 \text{ pulse}$ 

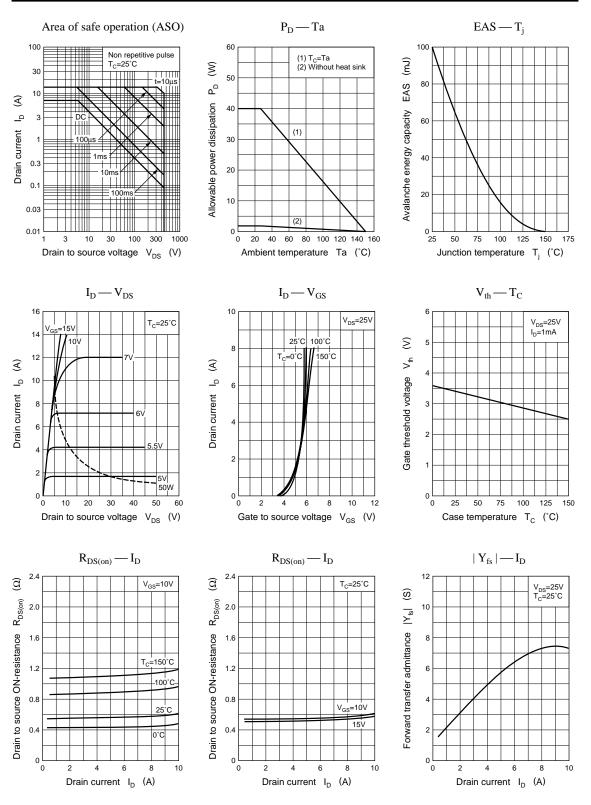
#### **Electrical Characteristics** ( $T_c = 25^{\circ}C$ )

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I <sub>DSS</sub>	$V_{DS} = 360V, V_{GS} = 0$		120	0.1	mA
Gate to Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30V, V_{DS} = 0$	1990	12.1	±1	μΑ
Drain to Source breakdown voltage	V <sub>DSS</sub>	$I_D = 1 \text{mA}, V_{GS} = 0$	450	1000		V
Gate threshold voltage	V <sub>th</sub>	$V_{DS} = 25V, I_D = 1mA$	2		5	V
Drain to Source ON-resistance	R <sub>DS(on)</sub>	$V_{GS} = 10V, I_D = 4A$		0.56	0.75	Ω
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = 25V, I_D = 4A$	3	5		S
Diode forward voltage	V <sub>DSF</sub>	$I_{DR} = 8A, V_{GS} = 0$			-1.7	V
Input capacitance (Common Source)	C <sub>iss</sub>			1300		pF
Output capacitance (Common Source)	C <sub>oss</sub>	$V_{DS} = 20V, V_{GS} = 0, f = 1MHz$		160		pF
Reverse transfer capacitance (Common Source)	C <sub>rss</sub>			70		pF
Turn-on time (delay time)	t <sub>d(on)</sub>			25		ns
RisetimeDF	t <sub>r</sub>	$V_{GS} = 10V, I_D = 4A$		45		ns
Turn-off time (dclay time)	t <sub>d(off)</sub>	$V_{DD} = 150V, R_L = 37.5\Omega$		150		ns
oEalldimec.com	t <sub>f</sub>			50		ns

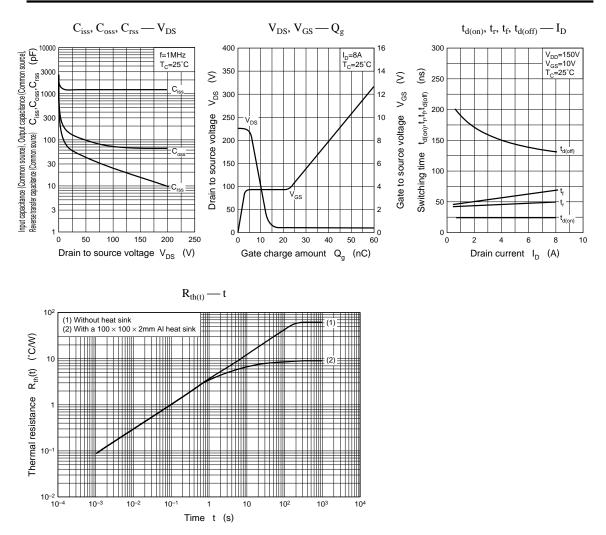


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### **Power F-MOS FETs**



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